Abstracts

A Monolithically Integrated F-Band Resistive InAIAs/InGaAs/InP HFET Mixer

C. Karlsson, N. Rorsman and H. Zirath. "A Monolithically Integrated F-Band Resistive InAIAs/InGaAs/InP HFET Mixer." 1995 Microwave and Guided Wave Letters 5.11 (Nov. 1995 [MGWL]): 394-395.

A monolithically inte grated F-band resistive HFET mixer has been designed, simulated, fabricated, and characterized. The mixer is based on an InAIAs/InGaAs/InP HFET with 0.15 µm gate length. The measured minimum conversion loss is 9 dB at 112.5 GHz and an LO power of 4 dBm, which is the lowest conversion loss reported for resistive HFET mixers in this frequency range.

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